

Abstract Submitted
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Superconductivity

and Magnetotransport of MBE grown Nb₂N/SiC and Nb₂N/AlN Heterostructures SURESH VISHWANATH, RUSEN YAN, ECE, Cornell University, Ithaca, NY-14853, SCOTT KATZER, NEERAJ NEPAL, BRIAN DOWNEY, DAVID MEYER, Electronics Science and Technology Division, U.S. NRL, Washington, DC 20375, GURU BAHADUR SINGH KHALSA, JOHN WRIGHT, MSE, Cornell University, Ithaca, NY 14853, YIMO HAN, DAVID MULLER, AEP, Cornell University, Ithaca, NY 14853, AMIT VERMA, IIT Kanpur, UP 208016, India, EDWARD LOCHOCKI, KYLE SHEN, Dept of Physics, Cornell University, Ithaca, NY 14853, HUILI GRACE XING, DEBDEEP JENA, ECE and MSE, Cornell University, Ithaca, NY 14853 — We find that plasma assisted molecular beam epitaxy (MBE) grown β -Nb₂N thin films [1] are metallic at room temperature, and undergo an electronic phase transition to the superconducting phase below about 10K. Hall-effect measurements reveal a bulk charge density of $\sim 4 \times 10^{23} \text{ cm}^{-3}$ and a mobility of 0.4-0.9 cm²/V.s. Superconducting transition temperature $T_c \sim 10\text{K}$, in-plane and out of plane critical magnetic field as a function of temperature have been obtained using resistivity and vibrating sample magnetometry measurements. Using this data, an Ioffe-Regel parameter of 10-15, a coherence length of 5-12 nm, and the London penetration depth have been estimated for various thickness of high quality epitaxial Nb₂N films. We will contrast transport and structural quality in MBE Nb₂N with well-studied NbN by a detailed analysis of aforesaid measurements along with X-Ray diffraction and Transmission-Electron Microscopy data. [1] D.S.Katzer et al., Appl. Phys. Express 8 085501 (2015)

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